## 150mA, 75V Switching Diode

## **FEATURES**

TAIWAN

• Low power loss, high efficiency

**IICONDUCTOR** 

- Ideal for automated placement
- High surge current capability
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC

Molding compound meets UL 94 V-0 flammability rating

• Terminal: Matte Au plated leads, solderable per J-STD-002

• Moisture sensitivity level: level 1, per J-STD-020 • Packing code with suffix "G" means green compound

Halogen-free according to IEC 61249-2-21

## **APPLICATIONS**

**MECHANICAL DATA** 

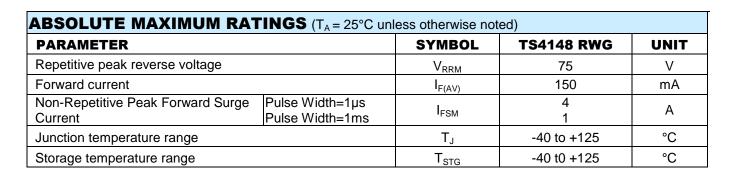
Switching mode power supply (SMPS)

• Meet JESD 201 class 1A whisker test Polarity: Indicated by cathode band • Weight: 6 mg (approximately)

KEY PARAMETERS					
PARAMETER	VALUE	UNIT			
I <sub>F(AV)</sub>	150	mA			
V <sub>RRM</sub>	75	V			
I <sub>FSM</sub>	4	А			
V <sub>F</sub> at I <sub>F</sub> =50mA	1	V			
T <sub>JMAX</sub>	125	°C			
Package	1005				
Configuration	Single dice				







THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-ambient thermal resistance	R <sub>eja</sub>	500	°C/W		

• Case: 1005

(halogen-free)



# TS4148 RWG Taiwan Semiconductor

ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	DITIONS SYMBOL		MAX	UNIT	
Forward voltage per diode (1)	$I_{F} = 50 \text{mA}, T_{J} = 25^{\circ}\text{C}$	V <sub>F</sub>	-	1	V	
Reverse current @ rated $V_R$ per diode $^{(2)}$	V <sub>R</sub> =20V T <sub>J</sub> = 25°C		-	25	nA	
	V <sub>R</sub> =75V T <sub>J</sub> = 25°C	I <sub>R</sub>	-	2.5	μA	
Junction capacitance	1 MHz, V <sub>R</sub> =0V	CJ	-	4	pF	

#### Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION					
PART NO.	PACKING PACKING CODE CODE SUFFIX(*)		PACKAGE	PACKING	
TS4148 (Note 1)	RW	G	1005	4K / 7" Reel	

Notes:

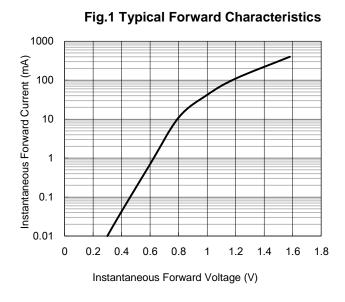
\*: optional available

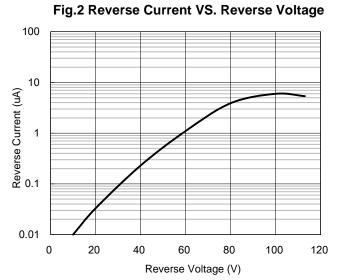
EXAMPLE						
EXAMPLE P/N	EXAMPLE P/N PART NO. PACKING CODE		PACKING CODE SUFFIX	DESCRIPTION		
TS4148 RWG	TS4148	RW	G	Green compound		



#### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)





#### Fig.3 Admissible Power Dissipation Curve

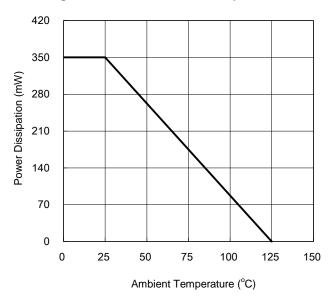
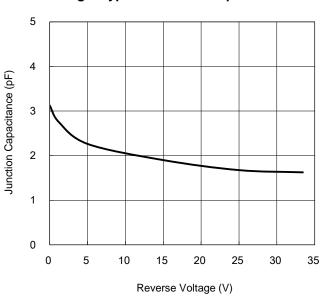


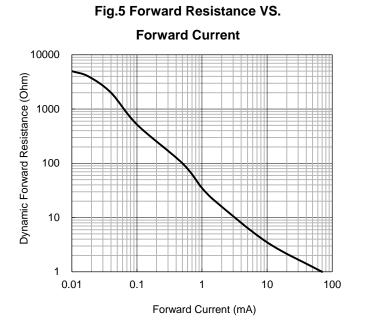
Fig.4 Typical Junction Capacitance





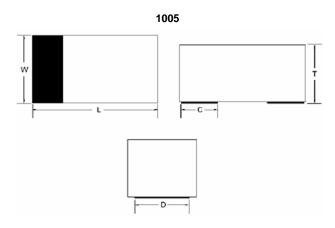
#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 





#### PACKAGE OUTLINE DIMENSION



DIM.		Unit(mn	n)	Unit(inch)		
	Min	Тур	Max	Min	Тур	Max
L	2.40	-	2.60	0.094	-	0.102
W	1.10	-	1.30	0.043	-	0.051
Т	0.70	-	0.90	0.028	-	0.035
С	-	0.50	-	-	0.020	-
D	-	1.00	-	-	0.039	-

#### **MARKING DIAGRAM**





Taiwan Semiconductor

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